



# TECHNICAL DATA

## PNP POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/545

### Devices

2N5151  
2N5151L

2N5153  
2N5153L

### Qualified Level

JAN  
JANTX  
JANTXV

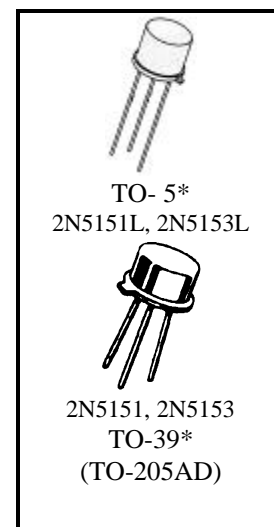
### MAXIMUM RATINGS

Ratings	Symbol	All Units	Units
Collector-Emitter Voltage	$V_{CEO}$	80	Vdc
Collector-Base Voltage	$V_{CBO}$	100	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.5	Vdc
Collector Current	$I_C^{(3,4)}$	2.0	Adc
Total Power Dissipation	$P_T$	@ $T_A = +25^{\circ}C^{(1)}$	1.0
		@ $T_C = +25^{\circ}C^{(2)}$	11.8
Operating & Storage Temperature Range	$T_j, T_{stg}$	-65 to +200	$^{\circ}C$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	15	$^{\circ}C/W$

- 1) Derate linearly 5.7 mW/ $^{\circ}C$  for  $T_A > +25^{\circ}C$
- 2) Derate linearly 66.7 mW/ $^{\circ}C$  for  $T_C > +25^{\circ}C$
- 3) Derate linearly 6.67 mW/ $^{\circ}C$  for  $T_A > +25^{\circ}C$
- 4) Derate linearly 80 mW/ $^{\circ}C$  for  $T_C > +25^{\circ}C$



\*See appendix A for package outline

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 100$ mAdc, $I_B = 0$	$V_{(BR)CEO}$	80		Vdc
Emitter-Base Cutoff Current $V_{EB} = 4.0$ Vdc, $I_C = 0$ $V_{EB} = 5.5$ Vdc, $I_C = 0$	$I_{EBO}$		1.0	$\mu$ Adc
			1.0	mAdc
Collector-Emitter Cutoff Current $V_{CE} = 60$ Vdc, $V_{BE} = 0$ $V_{CE} = 100$ Vdc, $V_{BE} = 0$	$I_{CES}$		1.0	$\mu$ Adc
			1.0	mAdc
Collector-Base Cutoff Current $V_{CE} = 40$ Vdc, $I_B = 0$	$I_{CEO}$		50	$\mu$ Adc

6 Lake Street, Lawrence, MA 01841  
1-800-446-1158 / (978) 794-1666 / Fax: (978) 689-0803

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## 2N5151, 2N5153 JAN SERIES

**ELECTRICAL CHARACTERISTICS (con't)**

Characteristics	Symbol	Min.	Max.	Unit
<b>ON CHARACTERISTICS</b>				
Forward Current Transfer Ratio $I_C = 50 \text{ mA dc}, V_{CE} = 5 \text{ V dc}$	2N5151 2N5153	20 50		
$I_C = 2.5 \text{ A dc}, V_{CE} = 5 \text{ V dc}$	2N5151 2N5153	30 70	90 200	
$I_C = 5 \text{ A dc}, V_{CE} = 5 \text{ V dc}$	2N5151 2N5153	20 40		
Collector-Emitter Saturation Voltage $I_C = 2.5 \text{ A dc}, I_B = 250 \text{ A dc}$ $I_C = 5 \text{ A dc}, I_B = 500 \text{ A dc}$	$V_{CE(sat)}$		0.75 1.5	Vdc
Base-Emitter Voltage nonsaturated $V_{CE} = 5 \text{ V dc}, I_C = 2.5 \text{ A dc}$	$V_{BE}$		1.45	Vdc
Base-Emitter Saturation Voltage $I_C = 2.5 \text{ A dc}, I_B = 250 \text{ mA dc}$ $I_C = 5 \text{ A dc}, I_B = 500 \text{ mA dc}$	$V_{BE(sat)}$		1.45 2.2	Vdc

**DYNAMIC CHARACTERISTICS**

Magnitude of Common Emitter Small-Signal Short Circuit Forward-Current Transfer Ratio $I_C = 500 \text{ mA dc}, V_{CE} = 5 \text{ V dc}, f = 10 \text{ MHz}$	$ h_{fe} $	6 7		
Common-Emitter Small-Signal Short-Circuit Forward-Current Transfer Ratio $I_C = 100 \text{ mA dc}, V_{CE} = 5 \text{ V dc}, f = 1 \text{ kHz}$	$h_{fe}$	20 50		
Output Capacitance $V_{CB} = 10 \text{ V dc}, I_E = 0, f = 1.0 \text{ MHz}$	$C_{obo}$		250	pF

**SWITCHING CHARACTERISTICS**

Turn-On Time $I_C = 5 \text{ A dc}, I_{B1} = 500 \text{ mA dc}$	$t_{on}$		0.5	$\mu\text{s}$
Turn-Off Time $R_L = 6\Omega$	$t_{off}$		1.5	$\mu\text{s}$
Storage Time $I_{B2} = -500 \text{ mA dc}$	$t_s$		1.4	$\mu\text{s}$
Fall Time $V_{BE(OFF)} = 3.7 \text{ V dc}$	$t_f$		0.5	$\mu\text{s}$

**SAFE OPERATING AREA**

DC Tests $T_C = +25^\circ\text{C}, 1 \text{ Cycle}, t_p = 1.0 \text{ s}$ <b>Test 1</b> $V_{CE} = 5.8 \text{ V dc}, I_C = 2.0 \text{ A dc}$ <b>Test 2</b> $V_{CE} = 32 \text{ V dc}, I_C = 340 \text{ mA dc}$ <b>Test 3</b> $V_{CE} = 80 \text{ V dc}, I_C = 20 \text{ mA dc}$
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